MOSFETs Silicon N-Channel MOS

# SSM6K202FE

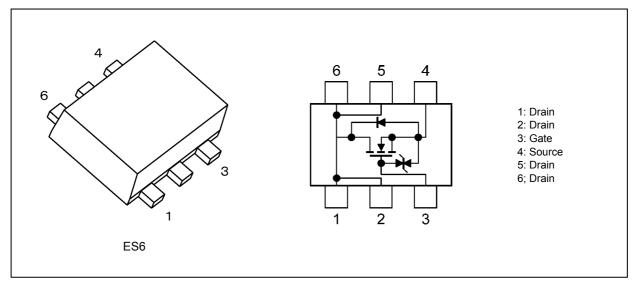
#### 1. Applications

- High-Speed Switching
- Power Management Switches

### 2. Features

- (1) 1.8-V drive
- (2) Low drain-source on-resistance
  - $\begin{array}{l} : {\rm R}_{\rm DS(ON)} = 145 \ {\rm m}\Omega \ ({\rm max}) \ (@V_{\rm GS} = 1.8 \ {\rm V}) \\ {\rm R}_{\rm DS(ON)} = 101 \ {\rm m}\Omega \ ({\rm max}) \ (@V_{\rm GS} = 2.5 \ {\rm V}) \\ {\rm R}_{\rm DS(ON)} = 85 \ {\rm m}\Omega \ ({\rm max}) \ (@V_{\rm GS} = 4.0 \ {\rm V}) \end{array}$

### 3. Packaging and Internal Circuit



### 4. Absolute Maximum Ratings (Note) (Unless otherwise specified, $T_a = 25$ °C)

| Cha                    | acteristics        | Symbol           | Rating     | Unit |
|------------------------|--------------------|------------------|------------|------|
| Drain-source voltage   |                    | V <sub>DSS</sub> | 30         | V    |
| Gate-source voltage    |                    | V <sub>GSS</sub> | ±12        | V    |
| Drain current (DC)     | (Note 1)           | I <sub>D</sub>   | 2.3        | A    |
| Drain current (pulsed) | (Note 1), (Note 2) | I <sub>DP</sub>  | 4.6        |      |
| Power dissipation      | (Note 3)           | PD               | 500        | mW   |
| Channel temperature    |                    | T <sub>ch</sub>  | 150        | °C   |
| Storage temperature    |                    | T <sub>stg</sub> | -55 to 150 | °C   |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2: Pulse width (PW)  $\leq$  10 ms, duty  $\leq$  1%

Note 3: Device mounted on an FR4 board. (25.4 mm  $\times$  25.4 mm  $\times$  1.6 mm ,Cu pad: 645 mm<sup>2</sup>)

- Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.
- Note: The channel-to-ambient thermal resistance, R<sub>th(ch-a)</sub>, and the drain power dissipation, P<sub>D</sub>, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

### 5. Electrical Characteristics

### 5.1. Static Characteristics (Unless otherwise specified, $T_a = 25$ °C)

| Characteristics                |          | Symbol               | Test Condition                                  | Min | Тур. | Max | Unit |
|--------------------------------|----------|----------------------|---|-----|------|-----|------|
| Drain-source breakdown voltage |          | V <sub>(BR)DSS</sub> | I <sub>D</sub> = 1 mA, V <sub>GS</sub> = 0 V    | 30  | —    | _   | V    |
| Drain-source breakdown voltage |          | V <sub>(BR)DSX</sub> | I <sub>D</sub> = 1 mA, V <sub>GS</sub> = -12 V  | 18  | _    | _   |      |
| Drain cut-off current          |          | I <sub>DSS</sub>     | $V_{DS}$ = 30 V, $V_{GS}$ = 0 V                 | —   | _    | 1   | μA   |
| Gate leakage current           |          | I <sub>GSS</sub>     | $V_{DS}$ = 0 V, $V_{GS}$ = ±12 V                | _   | _    | ±1  | μA   |
| Gate threshold voltage         | (Note 1) | V <sub>th</sub>      | V <sub>DS</sub> = 3 V, I <sub>D</sub> = 1 mA    | 0.4 | _    | 1.0 | V    |
| Drain-source on-resistance     | (Note 2) | R <sub>DS(ON)</sub>  | I <sub>D</sub> = 1.5 A, V <sub>GS</sub> = 4.0 V | _   | 66   | 85  | mΩ   |
|                                |          |                      | I <sub>D</sub> = 1.0 A, V <sub>GS</sub> = 2.5 V | _   | 78   | 101 |      |
|                                |          |                      | I <sub>D</sub> = 0.5 A, V <sub>GS</sub> = 1.8 V | _   | 95   | 145 |      |
| Forward transfer admittance    | (Note 2) | Y <sub>fs</sub>      | V <sub>DS</sub> = 3 V, I <sub>D</sub> = 1.5 A   | 3.9 | 7.8  | —   | S    |

Note 1: Let  $V_{th}$  be the voltage applied between gate and source that causes the drain current (I<sub>D</sub>) to below (1 mA for this device). Then, for normal switching operation,  $V_{GS(ON)}$  must be higher than  $V_{th}$ , and  $V_{GS(OFF)}$  must be lower than  $V_{th}$ . This relationship can be expressed as:  $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$ . Take this into consideration when using the device.

Note 2: Pulse measurement.

### 5.2. Dynamic Characteristics (Unless otherwise specified, $T_a = 25$ °C)

| Characteristics                | Symbol           | Test Condition   | Min | Тур. | Max | Unit |
|--------------------------------|------------------|--|-----|------|-----|------|
| Input capacitance              | C <sub>iss</sub> | V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V,   | _   | 270  | _   | pF   |
| Reverse transfer capacitance   | C <sub>rss</sub> | f = 1 MHz  | _   | 47   | _   |      |
| Output capacitance             | C <sub>oss</sub> |  | _   | 56   | _   | ]    |
| Switching time (turn-on time)  | t <sub>on</sub>  | $V_{DD}$ = 10 V, I <sub>D</sub> = 2 A,<br>V <sub>GS</sub> = 0 to 2.5 V, R <sub>G</sub> = 4.7 Ω | _   | 20   | —   | ns   |
| Switching time (turn-off time) | t <sub>off</sub> | Duty $\leq$ 1%, Input: t <sub>r</sub> , t <sub>f</sub> < 5 ns<br>Common source                 | _   | 31   | _   |      |

### 5.3. Switching Time Test Circuit

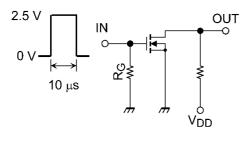


Fig. 5.3.1 Switching Time Test Circuit Fig. 5.3.2

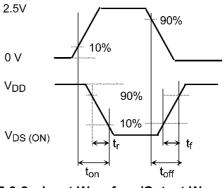


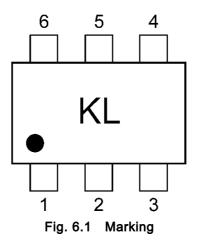
Fig. 5.3.2 Input Waveform/Output Waveform

### 5.4. Source-Drain Characteristics (Unless otherwise specified, $T_a = 25$ °C)

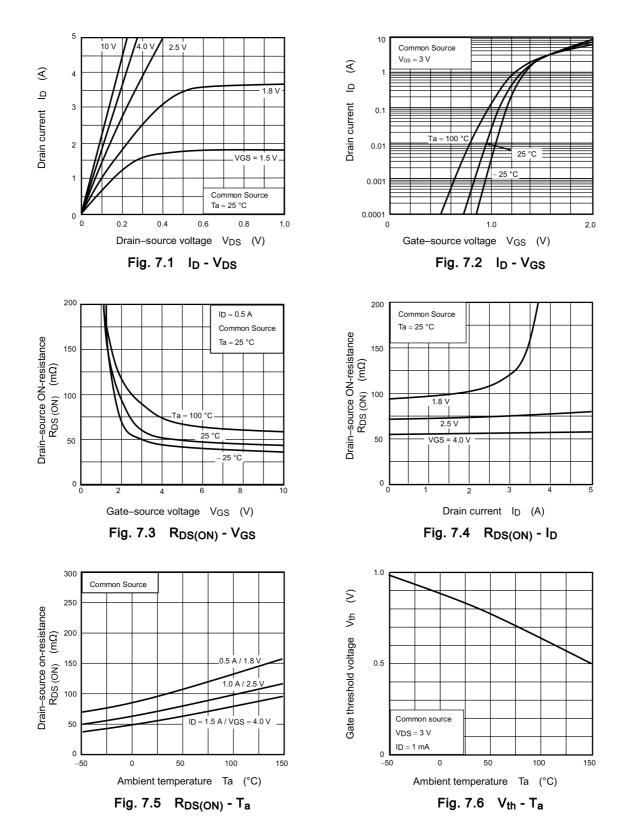
| Characteristics       |          | Symbol           | Test Condition                           | Min | Тур.  | Max  | Unit |
|-----------------------|----------|------------------|--|-----|-------|------|------|
| Diode forward voltage | (Note 1) | $V_{\text{DSF}}$ | $I_{\rm D}$ = -2.3 A, $V_{\rm GS}$ = 0 V | _   | -0.85 | -1.2 | V    |

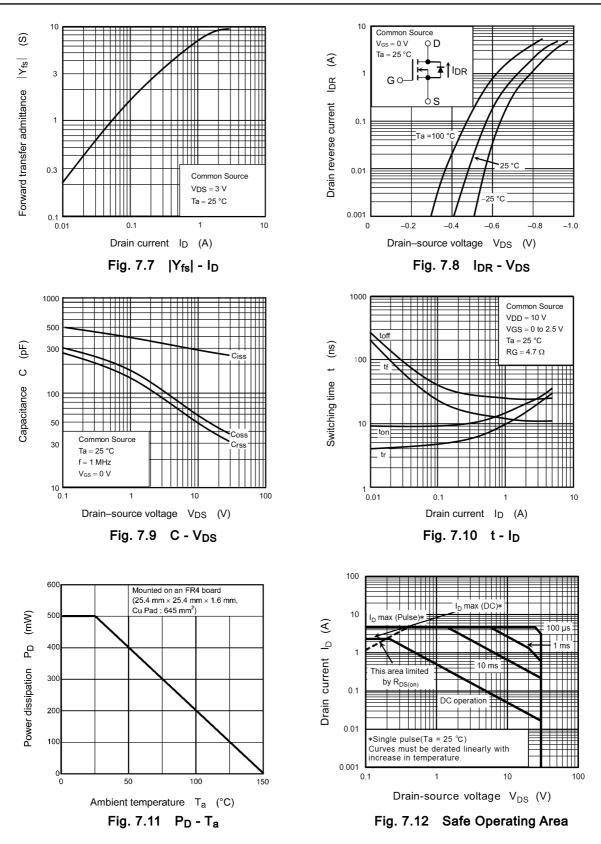
Note 1: Pulse measurement.

### 6. Marking



### 7. Characteristics Curves (Note)





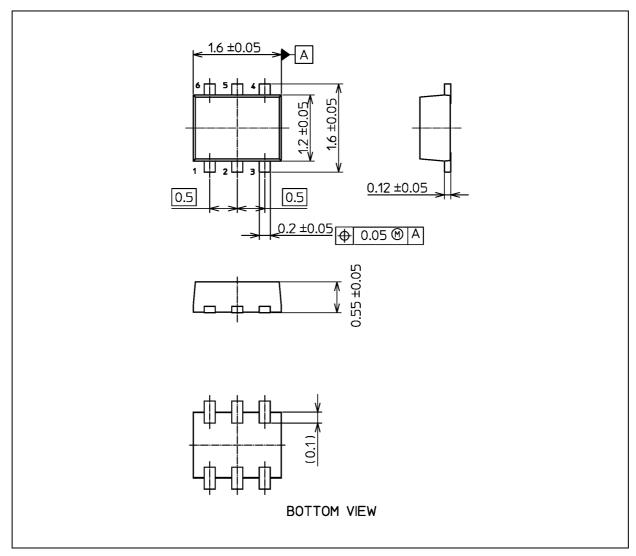
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



### SSM6K202FE

#### Package Dimensions

Unit: mm



Weight: 3.0 mg (typ.)

|               | Package Name(s) |
|---------------|-----------------|
| Nickname: ES6 |                 |

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